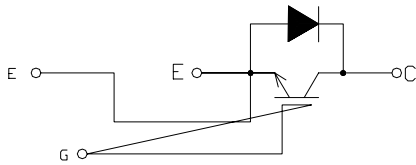
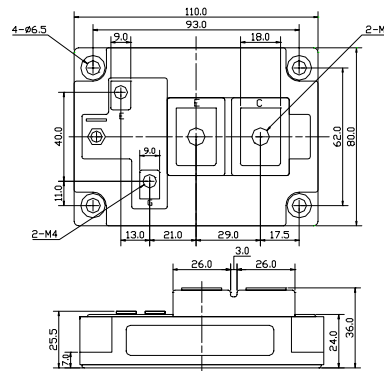


CIRCUIT



OUTLINE DRAWING



Dimension(mm)

Approximate Weight : 650g

MAXIMUM RATINGS (T_c=25°C)

Item		Symbol	PHMB800B12		Unit	
Collector-Emitter Voltage		V _{CEs}	1200		V	
Gate - Emitter Voltage		V _{GES}	+/- 20		V	
Collector Current	DC	I _C	800		A	
	1 ms	I _{CP}	1600			
Collector Power Dissipation		P _C	3100		W	
Junction Temperature Range		T _j	-40 to +150		°C	
Storage Temperature Range		T _{stg}	-40 to +125		°C	
Isolation Voltage (Terminal to Base AC, 1 min.)		V _{ISO}	2500		V	
Mounting Torque	Module Base to Heatsink	F _{TOR}	3		N•m	
	Bus Bar to Main Terminals		M4	1.4		
			M8	10.5		

ELECTRICAL CHARACTERISTICS (T_c=25°C)

Characteristic		Symbol	Test Condition	Min.	Typ.	Max.	Unit
Collector-Emitter Cut-Off Current		I _{CES}	V _{CE} =1200V, V _{GE} =0V	-	-	16.0	mA
Gate-Emitter Leakage Current		I _{GES}	V _{GE} =+/- 20V, V _{CE} =0V	-	-	1.0	μA
Collector-Emitter Saturation Voltage		V _{CE(sat)}	I _C =800A, V _{GE} =15V	-	1.9	2.4	V
Gate-Emitter Threshold Voltage		V _{GE(th)}	V _{CE} =5V, I _C =800mA	4.0	-	8.0	V
Input Capacitance		C _{ies}	V _{CE} =10V, V _{GE} =0V, f=1MHz	-	66000	-	pF
Switching Time	Rise Time	t _r	V _{CC} = 600V R _L = 0.75 ohm R _C = 0.5 ohm V _{GE} = +/- 15V	-	0.25	0.45	μs
	Turn-on Time	t _{on}		-	0.40	0.70	
	Fall Time	t _f		-	0.25	0.35	
	Turn-off Time	t _{off}		-	0.80	1.10	

FREE WHEELING DIODES RATINGS & CHARACTERISTICS (T_c=25°C)

Item		Symbol	Rated Value		Unit
Forward Current	DC	I _F	800		A
	1 ms	I _{FM}	1600		

Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Peak Forward Voltage	V _F	I _F =800A, V _{GE} =0V	-	1.9	2.4	V
Reverse Recovery Time	t _{rr}	I _F =800A, V _{GE} =-10V, di/dt=1600A/μs	-	0.25	0.35	μs

THERMAL CHARACTERISTICS

Characteristic		Symbol	Test Condition	Min.	Typ.	Max.	Unit
Thermal Impedance	IGBT	R _{th(j-c)}	Junction to Case	-	-	0.036	°C/W
	DIODE			-	-	0.065	

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Fig.1- Output Characteristics (Typical)

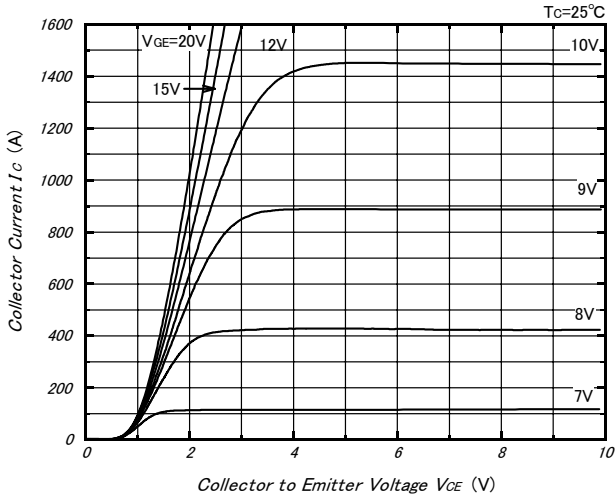


Fig.2- Collector to Emitter On Voltage vs. Gate to Emitter Voltage (Typical)

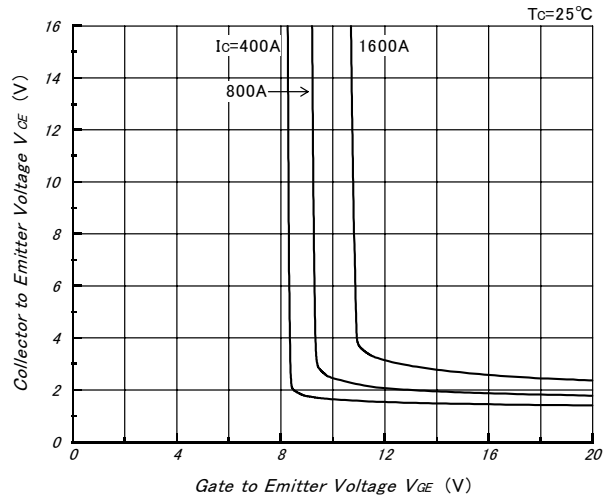


Fig.3- Collector to Emitter On Voltage vs. Gate to Emitter Voltage (Typical)

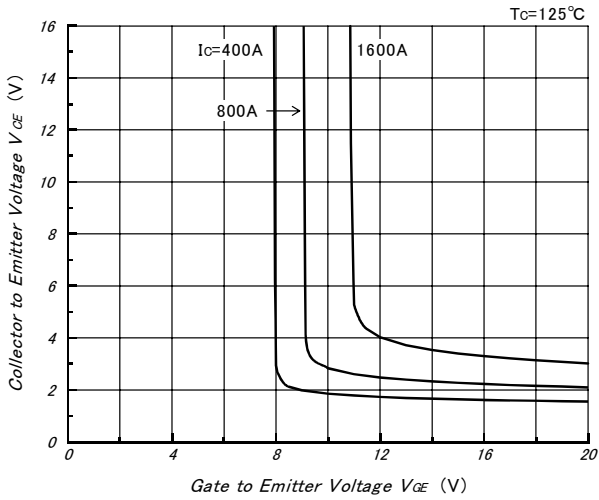


Fig.4- Gate Charge vs. Collector to Emitter Voltage (Typical)

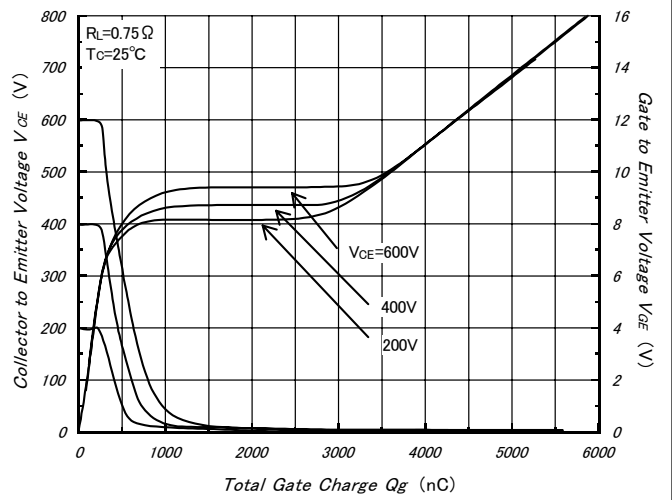


Fig.5- Capacitance vs. Collector to Emitter Voltage (Typical)

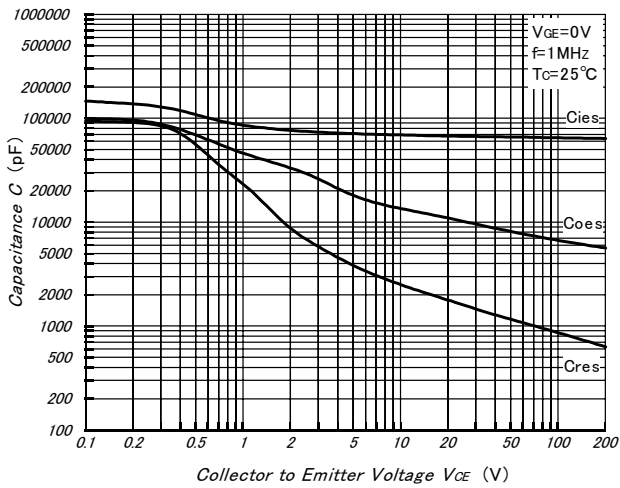
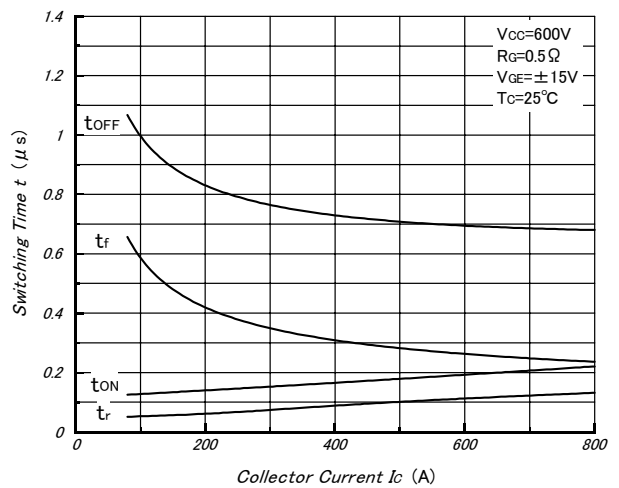


Fig.6- Collector Current vs. Switching Time (Typical)



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Fig.7- Series Gate Impedance vs. Switching Time (Typical)

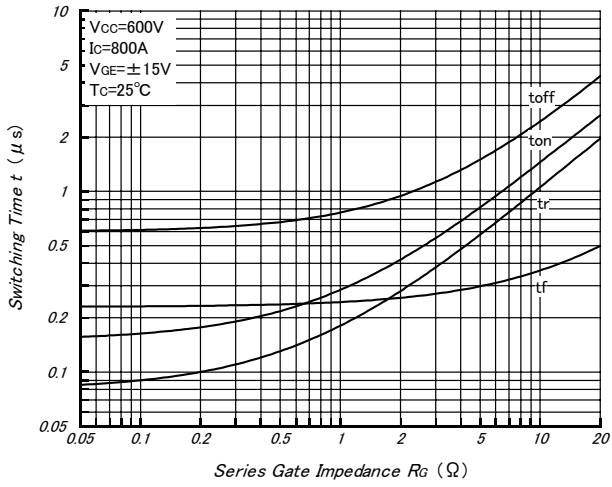


Fig.8- Forward Characteristics of Free Wheeling Diode (Typical)

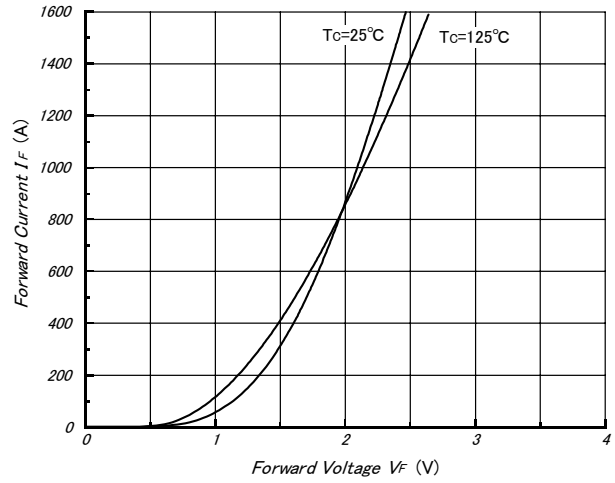


Fig.9- Reverse Recovery Characteristics (Typical)

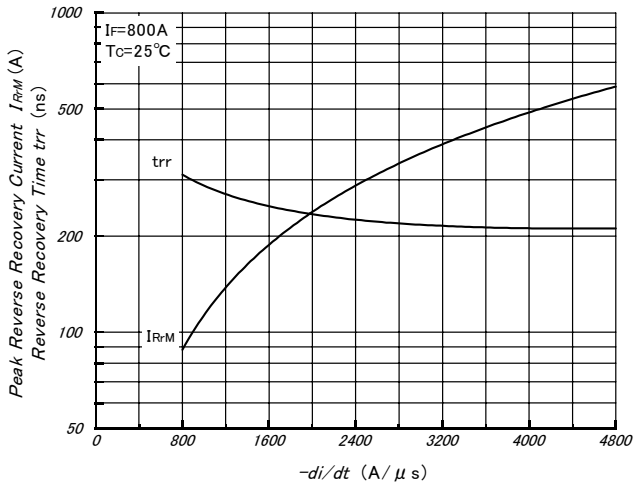


Fig.10- Reverse Bias Safe Operating Area (Typical)

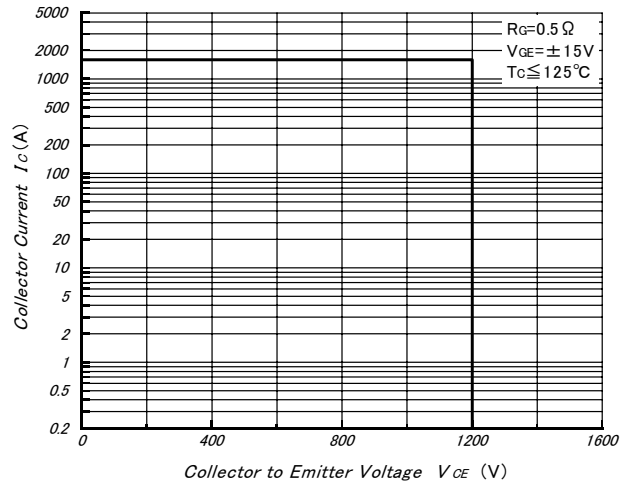


fig11-Transient Thermal Impedance

